
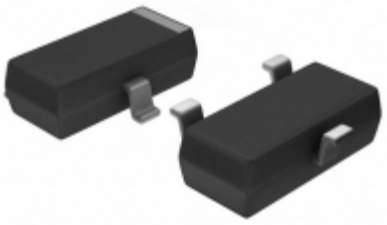
	<p>SI2312BDS-T1-GE3</p>
	<p>Hersteller-Teilenummer: SI2312BDS-T1-GE3</p> <p>Hersteller / Marke: Vishay / Siliconix</p> <p>Teil der Beschreibung: MOSFET N-CH 20V 3.9A SOT23-3</p> <p>Datenblätter:  SI2312BDS-T1-GE3.pdf</p> <p>RoHs Status: Bleifrei / RoHS-konform</p> <p>Lagerzustand: New original, 179033 pcs Stock Available.</p> <p>Liefern von: Hong Kong</p> <p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p>
	
<p>Image may be representation. See specs for product details.</p>	

Spezifikationen

Teilenummer	SI2312BDS-T1-GE3
Hersteller	Vishay / Siliconix
Beschreibung	MOSFET N-CH 20V 3.9A SOT23-3
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs,
Teilstatus	179033 pcs Stock
Serie	TrenchFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	TO-236-3, SC-59, SOT-23-3
Supplier Device-Gehäuse	SOT-23-3 (TO-236)
Verlustleistung (max)	750mW (Ta)
Typ FET	N-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	20V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	3.9A (Ta)
Rds On (Max) @ Id, Vgs	31 mOhm @ 5A, 4.5V
VGS (th) (Max) @ Id	850mV @ 250µA
Gate Charge (Qg) (Max) @ Vgs	12nC @ 4.5V
Eingabekapazität (Ciss) (Max) @ Vds	-
Antriebsspannung (Max Rds On, Min Rds On)	1.8V, 4.5V
Vgs (Max)	±8V
Verpackung	Tape & Reel (TR)















SI2312BDS-T1-GE3 ist neu im Original, Suche SI2312BDS-T1-GE3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI2312BDS-T1-GE3 Vishay / Siliconix mit Garantie und Vertrauen. Anfrage SI2312BDS-T1-GE3: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>SI2312BDS-T1 VISHAY VISHAY SOT23</p>	 <p>SI2312CDS-T1-E3 VISHA SI2312CDS-T1-E3 VISHA</p>	 <p>SI2312BDS-T1-E3 Vishay / Siliconix MOSFET N-CH 20V 3.9A SOT23-3</p>	 <p>SI2312D SI SI SOT-23</p>
 <p>SI2312CDS-T1-GE3 Vishay / Siliconix MOSFET N-CH 20V 6A SOT-23</p>	 <p>SI2312CDS-T1-GE3 Electro-Films (EFI) / Vishay MOSFET N-CH 20V 6A SOT-23</p>	 <p>SI2312BDS-T1-E3 Electro-Films (EFI) / Vishay MOSFET N-CH 20V 3.9A SOT23-3</p>	 <p>SI2312CDS 89K SI2312CDS 89K</p>

heiße Teile

Mehr

 SI2308DS-T1-GE3	 SI2309BDS-T1-E3	 SI2309BDS-T1-GE3	 SI2309CDS-T1-GE3	 SI2309CDS-T1-GE3
 SI2309DS	 SI2309DS-T1	 SI2309DS-T1-E3	 SI2309DS-T1-E3	 SI2309DS-T1-GE3
 SI2309DS-T1-E3	 SI2309DS/A92T	 SI2310DS	 SI2310DS-T1-E3	 SI2310DS-T1-GE3
 SI2311DS	 SI2311DS-T1	 SI2311DS-T1-E3	 SI2311DS-T1-E3	 SI2311DS-T1-GE3
 SI2311DS-T1-GE3	 SI2312BDS	 SI2312BDS-T1-E3	 SI2312BDS-T1-E3	 SI2312BDS-T1-GE3
 SI2312CDS-T1-E3	 SI2312CDS-T1-GE3	 SI2312CDS-T1-GE3	 SI2312DS	 SI2312DS-T1
 SI2312DS-T1-E3	 SI2312DS-T1-GE3	 SI2313DS	 SI2313DS-T1-E3	 SI2313DS-T1-GE3
 SI2314DS	 SI2314DS-T1-E3	 SI2314DS-T1-GE3	 SI2314EDS	 SI2314EDS-T1-E3
 SI2314EDS-T1-E3	 SI2314EDS-T1-GE3	 SI2314EDS-T1-GE3	 SI2315BDS	 SI2315BDS-T1-E3
 SI2315BDS-T1-E3	 SI2315BDS-T1-GE3	 SI2315BDS-T1-GE3	 SI2315DS	 SI2315DS-T1

Contact us: Info@Y-IC.com

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